



ASX RELEASE

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US PATENT GRANTED TO 4DS FOR ITS HETEROJUNCTION OXIDE NON-VOLATILE MEMORY DEVICES

4DS Memory Limited (ASX: 4DS) (**4DS**) today announced receiving its 16th patent granted by the United States Patent and Trademark Office (**USPTO**).

United States Patent Number 9,293,201 specifically relates to a heterojunction resistive memory device in conjunction with a thin-film access device.

The 4DS patent portfolio is based on wholly-owned, in-house developed, intellectual property created during the past eight years and contains both resistive random access memory (**ReRAM**) cell patents and PCMO deposition patents. An additional seven patent applications are in various stages of review at the USPTO.

Chief Executive Officer and Managing Director, Dr Guido Arnout said “The combination of a thin-film access device and our heterojunction cell is essential to the fabrication of 3D stacked ReRAMs required for mobile and cloud gigabyte silicon storage.

“Our unique patented non-filamentary ReRAM positions 4DS to deliver technology that enables memory to operate with lower power consumption, improved performance and increased processing efficiency when compared to traditional data storage technologies such as NAND Flash, a US\$40 billion market.”

In February 2016, 4DS announced the successful development of its scalable non-filamentary ReRAM cell at a 50 nanometre (**nm**) lithography, achieving wafer to wafer and lot to lot consistency using memory cells of varying sizes. The 50nm geometry parallels current 3D NAND Flash geometries and is essential for developing the high density gigabyte storage required in mobile devices and the cloud.

Achieving 50nm non-filamentary ReRAM cells with patent protection, when combined with thin-film access devices, positions 4DS as a pivotal technology provider for future 3D ReRAM for the fast-growing gigabyte silicon storage market.

Having achieved these critical milestones, the next development goal will demonstrate viable scalability below 50nm, with particular focus on endurance throughout the remainder of this year. Endurance defines how often a cell may reliably be written.

4DS will provide an investor update in April and throughout the year as development continues toward reliably and consistently fabricated smaller cell geometries.

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4DS Memory Limited (ASX:4DS), with research and development facilities located in Silicon Valley, is a developer of non-volatile memory technology, pioneering non-filamentary ReRAM for next generation storage in mobile and cloud. Established in 2007, 4DS owns a patented IP portfolio developed in house to create high density gigabyte storage.

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